MAPF-250128-150000

Linear RF Power TMOS **150W, 30MHz 100V**

M/A-COM Products Preliminary - Rev. 1108

Features

- Designed for Industrial, Scientific, Medical applications
- N-Channel enhancement mode MOSFET
- Specified 100V, 30MHz and 128MHz, Class AB
- Internally insulated Source terminals simplify heatsinking
- High Voltage Lower Current Less Circuit Loss
- Gold Metallization System for Reliability

Characteristics

Output Power = 150 Watts Power Gain = 20 dB (Typ, 30MHz), 15 dB (Typ, 128MHz)

ABSOLUTE MAXIMUM RATINGS AT 25°C

Parameter	Symbol	Rating	Units
Drain Source Voltage	V _{DS}	250	V
Gate Source Voltage	V _{DS}	+/-40	V
Drain Current	I _D	8.0(tbd)	A
Total Power Dissipation	P _D	300	W
Storage Temperature	T _{STG}	-65 to +150	°C
Junction Temperature	TJ	200	°C

4X .224" [A.69] 45.00 el 0257+ 0157 [28.04±0.38] TE CODE/LOT I **a**.ee on [12.19] ł .725" [18.42] .875" [24.77] ZX 8.125" [3.16] ZX R.125 [3.18] 4200 [12,70] .259"±.010" [4.59±0.25] 4X .005"±.001" [0.13±0.03] ŧ .100" [2.54] .10+±.010 [+.17±0.25] UNLESS OTHERWISE NOTED, TOLERANCES ARE INCHES ±.005" [MILLIMETERS ±0.13MM]

Case 211-11, Style 2

ELECTRICAL CHARACTERISTICS AT 25°C

Parameter	Symbol	Test Conditions	Min	Max	Units
Drain Source Breakdown Voltage	BV _{DSS}	I _D = 100mA	250	-	V
Drain Source Leakage Current	I _{DSS}	V _{DS} = 100 V	-	5	mA
Gate Source Leakage Current	I _{GSS}	V _{GS} = 10 V	-	1	μA
Forward Transconductance	G _M	I _{DS} =2.0 A, V _{DS} =10 V,	3	-	S
Gate Source Threshold Voltage	Vgs _(TH)	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 100 \text{mA}$	2	5	V
Drain Source On State Voltage	V _{DS(ON)}	V_{GS} =10V, I_{DS} = 5 A	-	6.6	V
Output Capacitance	C _{OSS}	$V_{\text{DS}} = 100 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1 \text{MHz}$	-	120	pF
Feedback Capacitance	C _{RSS}	$V_{\text{DS}} = 100 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1 \text{MHz}$	-	15	pF
Input Capacitance	C _{ISS}	V_{DS} = 100 V, V_{GS} =0V, f = 1 MHz	-	350	pF
Thermal Resistance	R _{THjc}	$V_{DS} = 100 V, P_{DISS} = 100W, Tj = 150 C$	-	0.6	°C/W

¹

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

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Preliminary - Rev. 1108

RF Electrical Characteristics at 25°C*

Parameter	Symbol	Test Conditions	Minimum	Maximum	Units
Power Gain	GP	$P_{out} = 150 W_{(PEP)}$	19		dB
		P _{out} = 150 W, F = 128 MHz CW	14		dB
Drain Efficiency	η	$P_{out} = 150 W_{(PEP)}$	40		%
		P _{out} = 150 W, F = 128 MHz CW	50		%
Intermodulation	IM3	$P_{out} = 150 W_{(PEP)},$		-30	dBc
Electrical Ruggedness	Ψ	P _{out} = 150 W _(PEP) , VSWR 5:1, 360°	No degradation		
CW Output Power at P1dB	P _{1DB}	V_{DD} =100 V, F= 30 MHz , I_{DQ} = 160mA	150		Watts
		V_{DD} =100 V, F=128 MHz , I_{DQ} = 160mA	150		Watts

* Test conditions unless otherwise specified: V_{DD} = 100V, I_{DQ} = 160 mA, F_1 = 30MHz, F_2 = F_1 +0.001MHz

Large Signal Impedance

 $V_{DD} = 100V; I_{DQ} = 160mA; P_{OUT} = 150W (PEP), 30MHz; P_{OUT} = 150W (P1dB), 128MHz$

F (MHz)	Z IN (Ω)	Z L(opt) (Ω)
30	5.09-j0.84	17.71+j14.21
128	1.90+j2.71	3.04+j7.08

 Z_{IN} = Complex conjugate of source impedance $Z_{L(OPT)}$ =Load impedance for optimum output power and IMD at specified voltage, quiescent current and efficiency.



2

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